

2 hot plate is disposed above said cool plate.

1 8. (new) A method for forming a coating film as defined in claim 3, wherein said
2 elevating means extends through said cool plate.

1 9. (new) A method for forming a coating film as defined in claim 1, wherein said
2 raw material is one of an inorganic SOG and an organic SOG.

1 A 10. (new) A method for forming a coating film as defined in claim 4, wherein
2 said interlayer insulation film has a dielectric constant of ≤ 3.5 .

1 11. (new) A method for forming a coating film as defined in claim 5, wherein
2 said interlayer insulation film has a dielectric constant of ≤ 3.5 .

1 12. (new) A method for forming a coating film as defined in claim 6, wherein
2 said interlayer insulation film has a dielectric constant of ≤ 3.5 .

IN THE ABSTRACT:

Line 2, change "The present invention aims at maintaining a low dielectric
constant in a case" to --A method--;

Line 3, after "film" insert --on a plate-like workpiece--; after "SOG" insert --so
as to maintain a low dielectric constant, involves the following steps--;

Lines 3-6, change the sentence "When a plate-like material ... is introduced into
the apparatus." to --Placing the workpiece, which has an applying film formed on its
surface, into a baking furnace--;

Line 6, before "the oxygen" insert --reducing--;

Line 7, change "atmosphere is reduced" to --furnace--; change "less than or